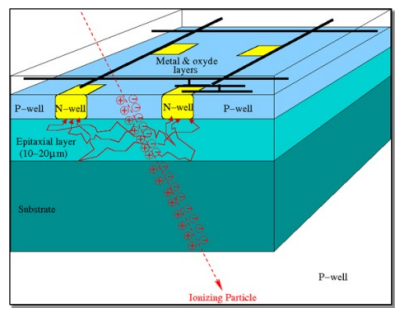
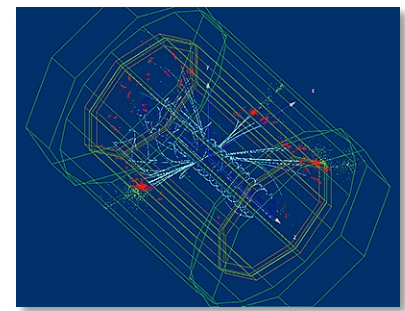


CMOS Pixel Sensors for an FCC Vertex Detector



Ziad EL BITAR, Auguste BESSON

On behalf of the
PICSEL group & C4PI Platform



PICSEL



C4PI-Platform



Outline

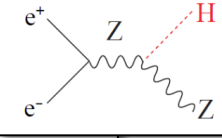
- Introduction: requirements & strategy
- MIMOSIS chip development (IPHC-IKF-GSI Collaboration)
- 65 nm R&D (with CERN EP R&D WP 1.2 & ALICE ITS-3)
- Stitching and bending
- Conclusion & Synergies in CMOS R&D

	Z	Higgs	ttbar
\sqrt{s} [GeV]	91.2	240	365
Luminosity / IP ($10^{34}\text{cm}^{-2}\text{s}^{-1}$)	230	8.5	1.7
no. of bunches / beam	16640	393	48
Bunch separation (ns)	20	994	3000

Higgs Factory Vertex detector requirements

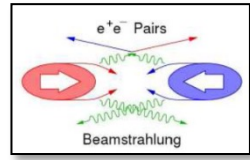
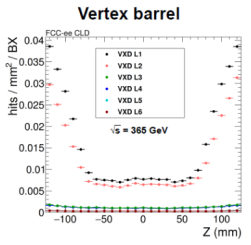
Physics

- ⇒ Flavour tagging
- ⇒ Low pT tracks
- ⇒ Vertex/Jet charge determination



Physics $O(\text{Hz}/\text{cm}^2)$

Beam background $O(10\text{-}50 \text{ MHz}/\text{cm}^2)$

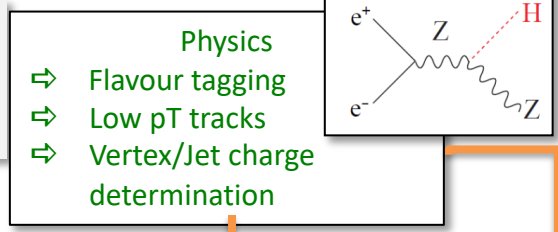
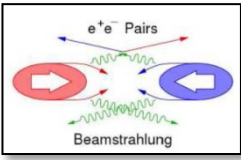
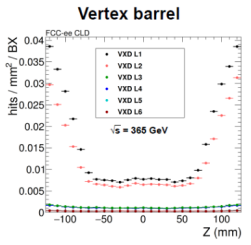


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- Physics
 - ⇒ Flavour tagging
 - ⇒ Low pT tracks
 - ⇒ Vertex/Jet charge determination

- Vertex reconstruction
 - ⇒ granularity
 - ⇒ Pitch $\sim 17\text{-}20 \mu\text{m}$
 - ⇒ $(\sigma_{sp} \sim 3\text{-}4 \mu\text{m})$

- Material Budget
 - ⇒ $\sim 0.15\% X_0$ / layer
 - ⇒ $< 1\% X_0$ for the whole VTX
 - + $\sim 0.3\% X_0$ for the beam pipe
 - + $0.15\% X_0$ for $5 \mu\text{m}$ Gold coating

Low material detectors & supports structures

$$\sigma_{d_0} = a \oplus \frac{b}{p \sin^{\frac{3}{2}} \theta}$$

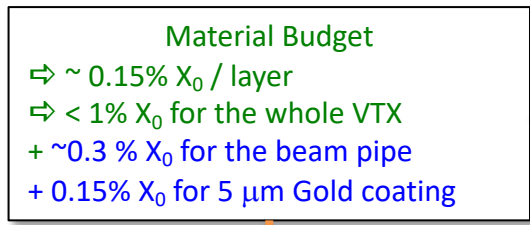
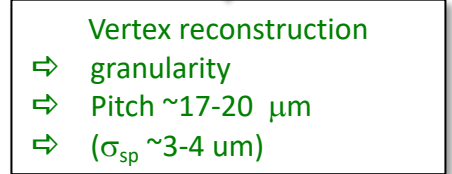
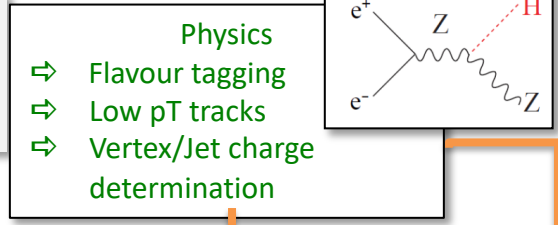
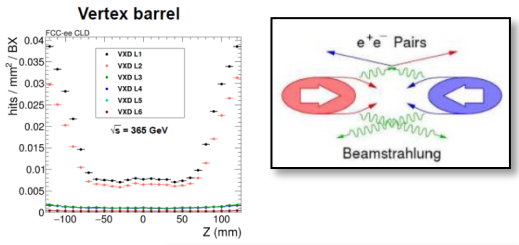
$a \simeq 5 \mu\text{m}$ $b \sim 15 \mu\text{m} \cdot \text{GeV}$ @ FCCee
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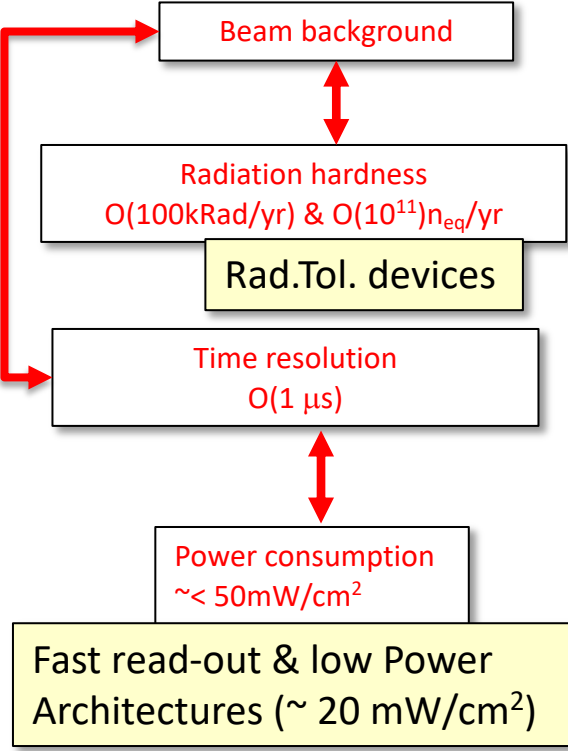
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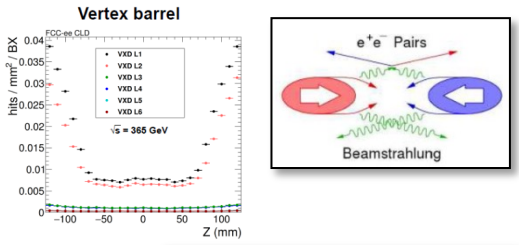
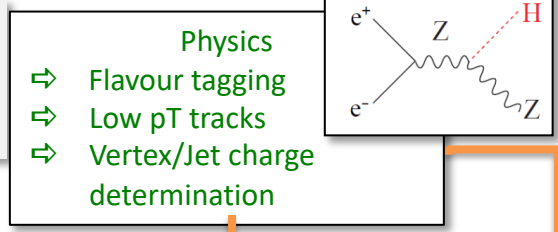
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Power pulsing (ILC) vs continuous beam (FCCee)

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Higgs Factory Vertex detector requirements



Physics $O(\text{Hz}/\text{cm}^2)$

Beam background $O(10\text{-}50 \text{ MHz}/\text{cm}^2)$

Beam background

Radiation hardness
 $O(100\text{kRad}/\text{yr})$ & $O(10^{11})n_{\text{eq}}/\text{yr}$

Rad.Tol. devices

Time resolution
 $O(1 \mu\text{s})$

Power consumption
 $\sim 50\text{mW}/\text{cm}^2$

Fast read-out & low Power Architectures ($\sim 20 \text{ mW}/\text{cm}^2$)

Power pulsing (ILC) vs continuous beam (FCCee)

Cooling
Stiffness / Alignment

Vertex reconstruction

- ⇒ granularity
- ⇒ Pitch $\sim 17\text{-}20 \mu\text{m}$
- ⇒ $(\sigma_{\text{sp}} \sim 3\text{-}4 \mu\text{m})$

Material Budget

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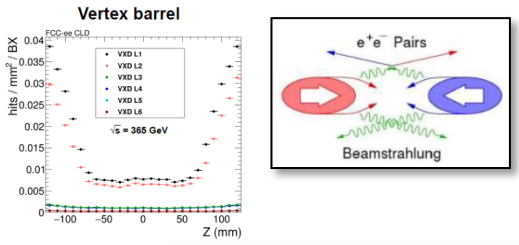
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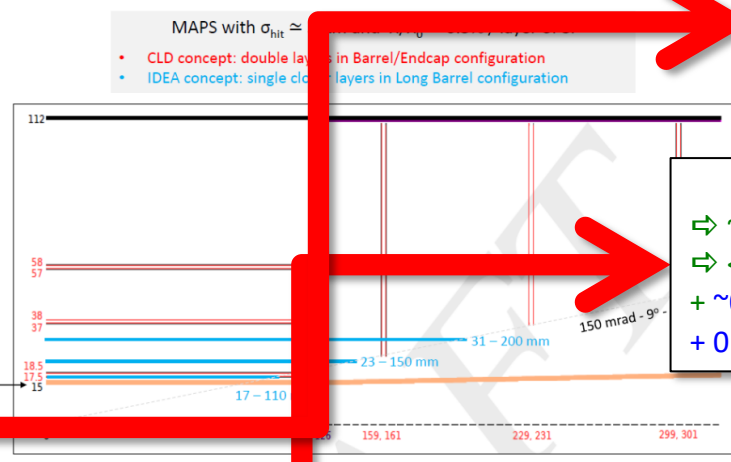
Physics $O(\text{Hz}/\text{cm}^2)$
Beam background $O(10\text{-}50 \text{ MHz}/\text{cm}^2)$
 CLD and IDEA Vertex Detectors designs (superimposed)

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(Figure: D. Contardo)

Beam background

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Power pulsing (ILC) vs continuous beam (FCCee)

5 single layers or 3 double layers ?
 Inner (1.7 cm or lower ?) and outer radius are key factors

Strategy: on the road to Higgs factories

Design, build and exploit CMOS pixels sensors
with low material budget & high granularity

In order to contribute to the construction of a vertex & a tracking detector in a Higgs factory.

Approach the Higgs factories
vertex detector requirements

MIMOSIS chip family (180 nm)



Maintain & develop the
know how to build sensors
to be installed in real
experiments

Input for detector simulations

Optimize the parameters
of the technology
(e.g. sensitive layer)

Exploit fully the potential
of the CMOS technology

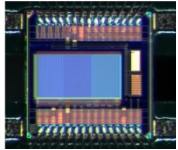
R&D 65 nm

Large surfaces
(stitching)

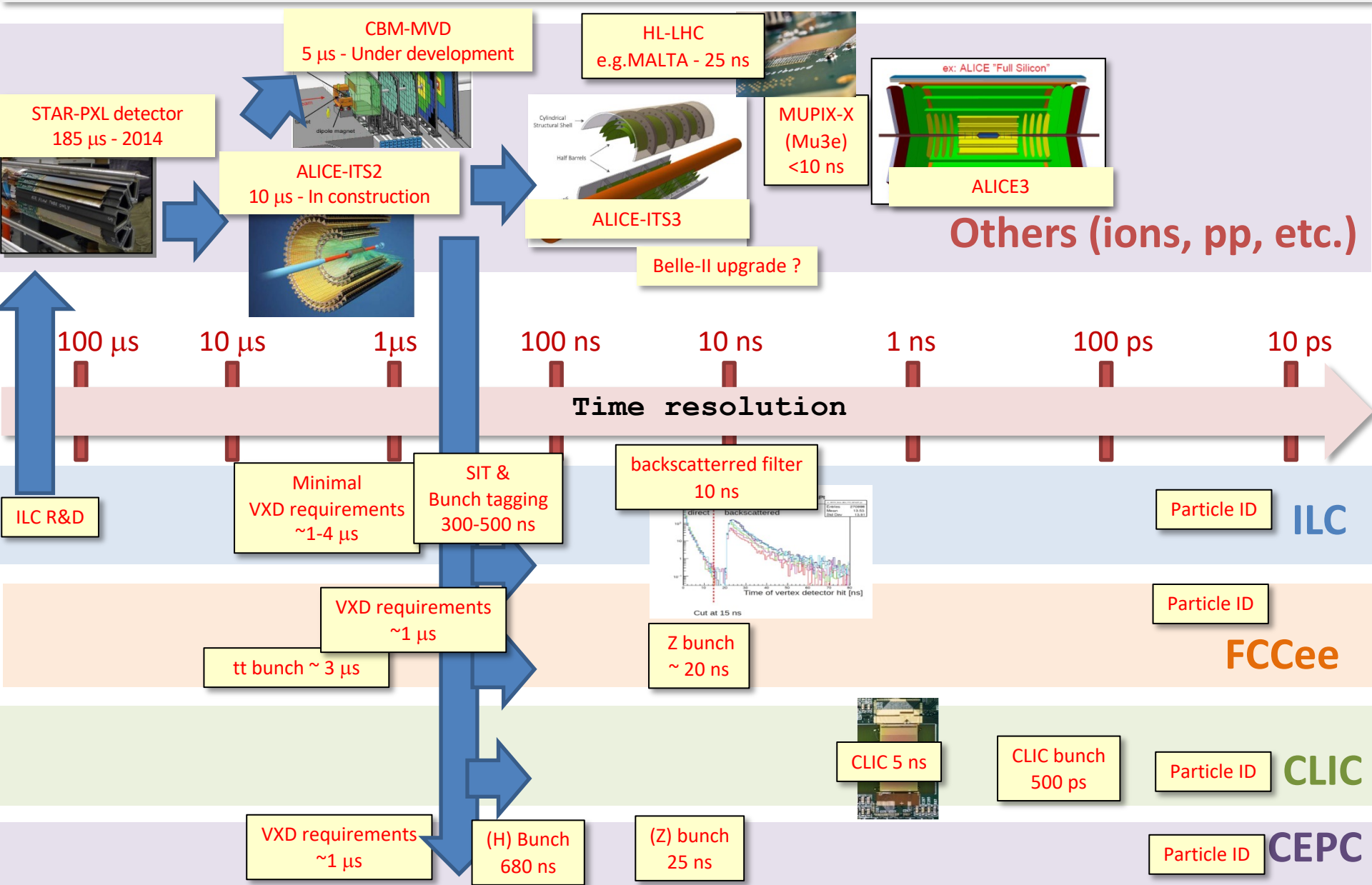
Bent sensors

Integration

Emerging technologies
(e.g. double tier)



Time resolution in the context of e^+e^- colliders



Synergies

K. Jakobs, FCC Physics Workshop, Feb 2022

ECFA recognizes the need for the experimental and theoretical communities involved in physics studies, experiment designs and detector technologies at future Higgs factories to gather. **ECFA supports a series of workshops** with the aim to **share challenges and expertise, to explore synergies in their efforts** and to respond coherently to this priority in the European Strategy for Particle Physics (ESPP).

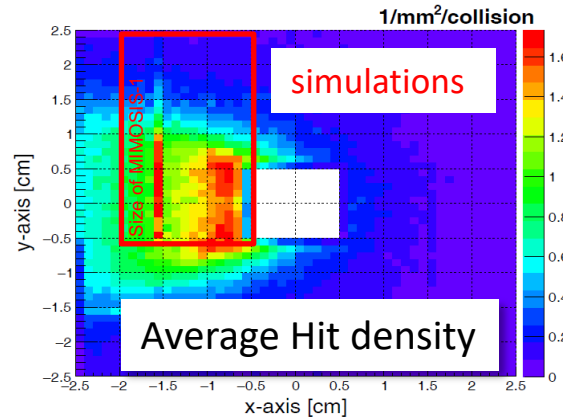
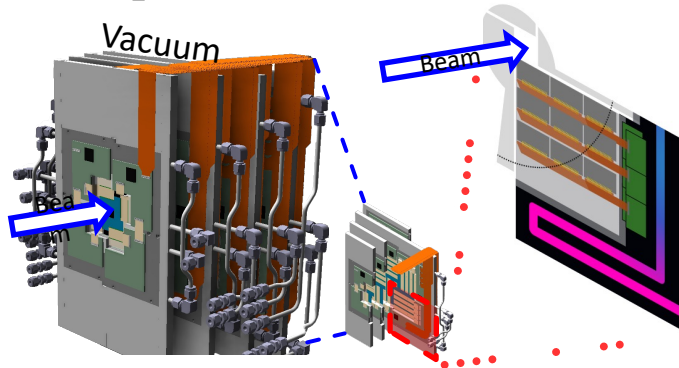
Goal: bring the entire e^+e^- Higgs factory effort together, foster cooperation across various projects; collaborative research programmes are to emerge



Important similarities between FCCee requirements & Heavy ions experiments (ALICE ITS3, ALICE3, EIC, etc.)

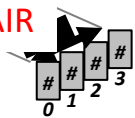
● Must happen or main physics goals cannot be met ● Important to meet several physics goals ● Desirable to enhance physics reach ● R&D needs being met

Requirements



Physics parameter	Requirements
Spatial resolution	~ 5 μm
Time resolution	~ 5 μs
Material budget	0.05% X_0
Power consumption	< 100 – 200 mW/cm^2
Operation temperature	- 40 $^\circ\text{C}$ to 30 $^\circ\text{C}$
Temp gradient on sensor	< 5K
Radiation tol* (non-ion)	~ $7 \times 10^{13} \text{ n}_{\text{eq}}/\text{cm}^2$
Radiation tol* (ionizing)	~ 5 MRad
Data flow (peak hit rate)	@ $7 \times 10^5 / (\text{mm}^2\text{s})$ > 2 Gbit/s

CBM-MVD@FAIR



- 4 double-sided thin planar detector stations
- 100 kHz Au+Au @ 11 AGeV and 10GHz p+Au @ 30 AGeV
- Non uniform hit density in time and space
- High radiation environment, operating in vacuum

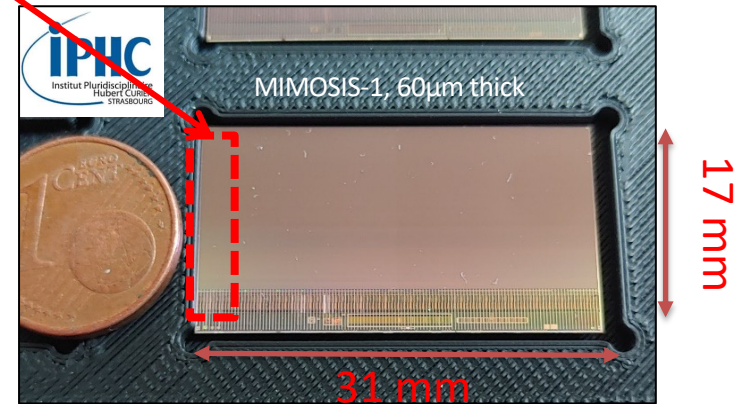
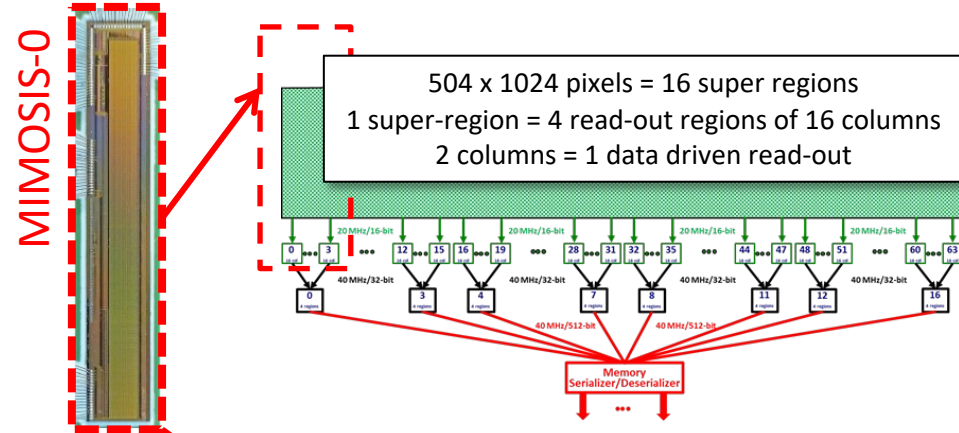
MIMOSIS chip

- ✓ Based on ALPIDE architecture
- ✓ Discriminator on $27 \times 30 \mu\text{m}^2$ pixel
- ✓ Multiple data concentration steps
- ✓ Elastic output buffer
- ✓ 8 x 320 Mbps links (switchable)
- ✓ Triple redundant electronics

Parameter	Value
Technology	TowerJazz 180 nm
Epi layer	~ 25 μm
Epi layer resistivity	> $1 \text{ k}\Omega \text{ cm}$
Sensor thickness	60 μm
Pixel size	$26.88 \mu\text{m} \times 30.24 \mu\text{m}$
Matrix size	1024×504 (516096 pix)
Matrix area	~ 4.2 cm^2
Matrix readout time	5 μs (event driven)
Power consumption	40-70 mW/cm^2

MIMOSIS roadmap

- 4 prototypes:
- MIMOSIS-0: = 2 regions
 - ✓ Tests (2018-2019)
 - Testability
- MIMOSIS-1: 1st full size prototype
 - ✓ Elastic buffer, SEE hardened
 - ✓ Fabricated in 2020
 - ✓ Lab/beam test campaign in 2021
- **MIMOSIS-2: Submitted last month (october 2022)**
 - ✓ On-chip clustering
 - ✓ Thicker epi layer tests
 - ✓ Test prototype for 1 μ s readout time
- MIMOSIS-3: final pre-production sensor
 - ✓ ≥ 2023



⇒ architecture adaptable to a fast sensor for a FCC vertex detector
⇒ Opportunity to study different designs/options

MIMOSIS-1

MIMOSIS tests

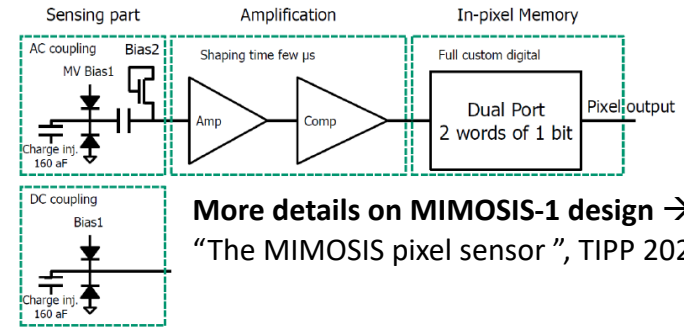
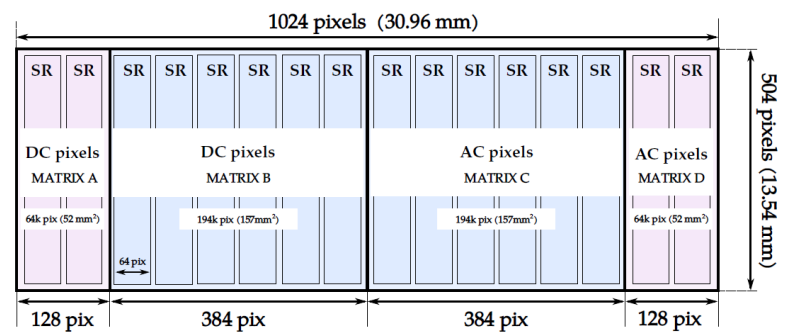
- ✓ Submatrices: DC/AC pixels
 - DC pixels: ALPIDE-derived
 - AC pixels: top bias up to > 20V
- ✓ 6 epitaxial variants (18 wafers)
 - Thinned down to 60 μm
 - Study Yield
 - Study charge collection / spatial res.
 - Explore performances after irradiation

Intense test program in 2021:

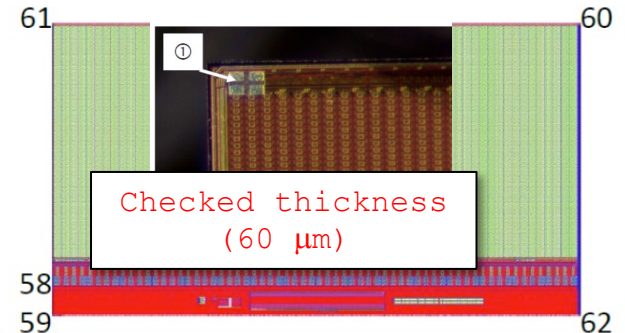
- ✓ Laboratory tests
- ✓ Irradiation tests

Ljubjana (TRIGA)	~1 MeV reactor neutrons
Karlsruhe (KIT)	~10 keV X-rays

- ✓ Beam tests @ DESY/CERN (3 campaigns)
- ✓ Latchup / SEE tests at GSI



More details on MIMOSIS-1 design → F. Morel, "The MIMOSIS pixel sensor", TIPP 2021

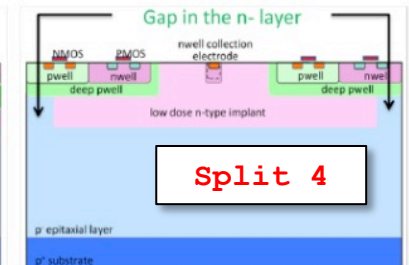
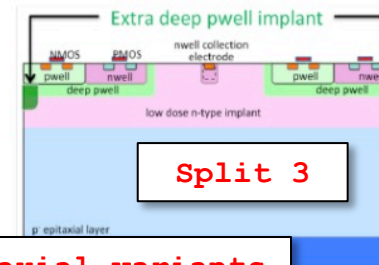
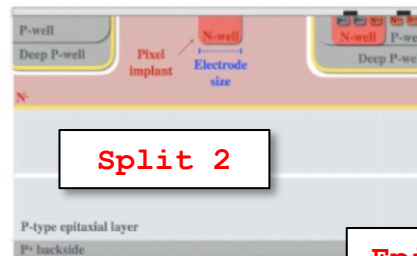


continuous n-layer

additional p-implant

gap in n-layer

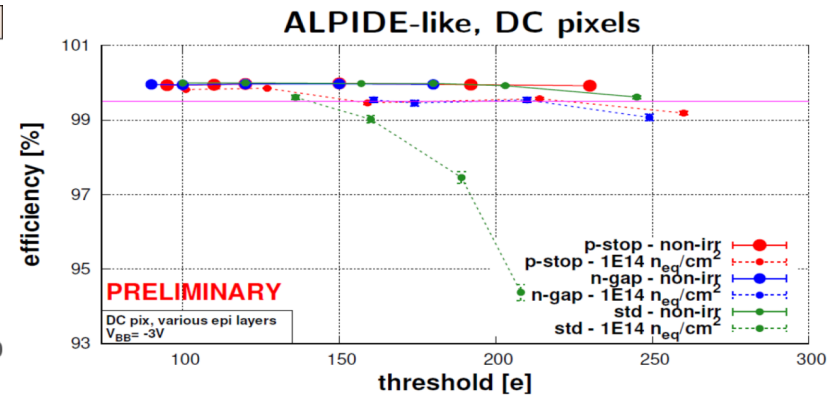
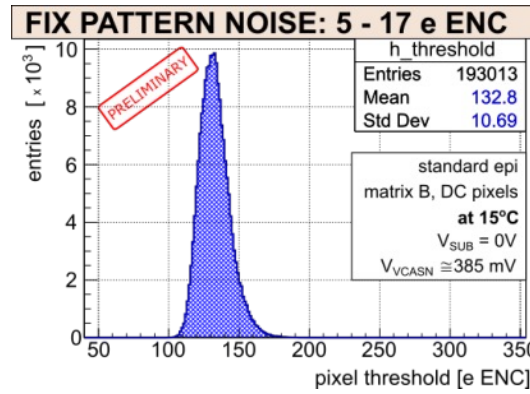
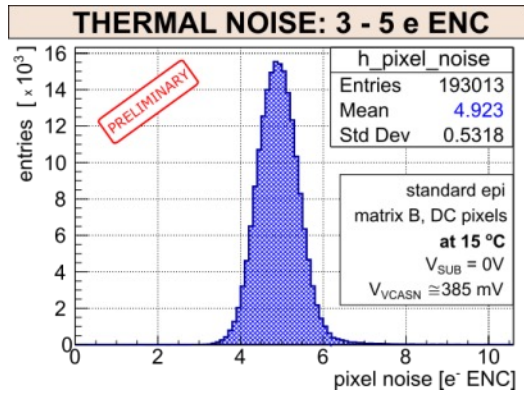
- standard process (3 available wafers)
- continuous n-layer (blanket) (3 wafers)
- additional p-implant (3 wafers)
- gap in n-layer (3 wafers)



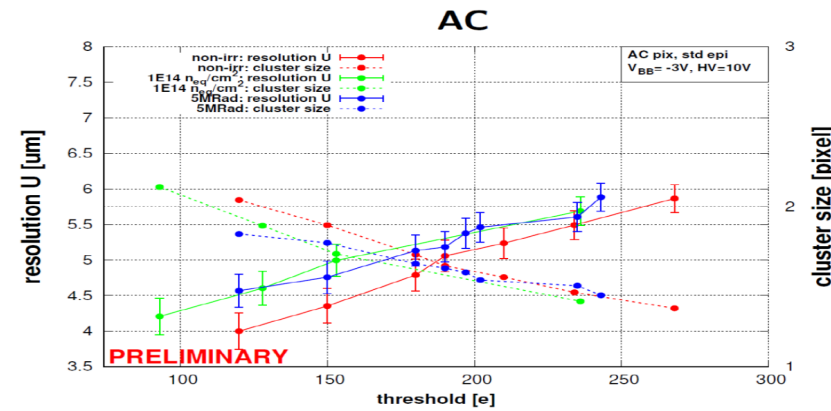
Epitaxial variants

Pic from: Munker, Vertex 2018, Status of silicon detector R&D at CLIC
Carlos, TREDI 2019, Results of the Malta CMOS pixel detector prototype for the ATLAS Pixel ITK

MIMOSIS beam test results



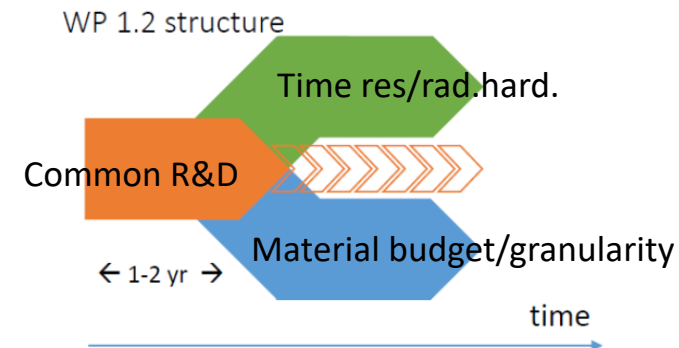
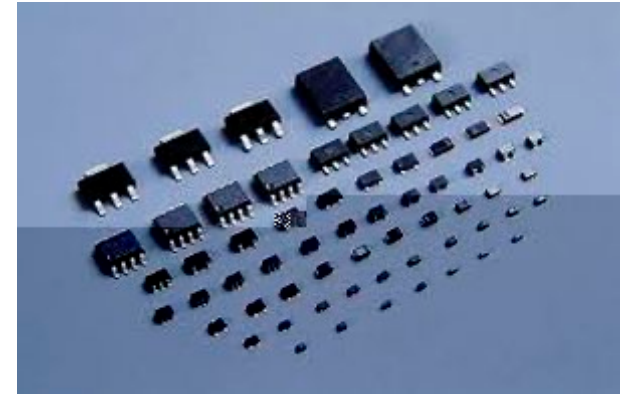
- Noise
 - ✓ DC pixels, (no back bias applied) @ room T°C
 - ✓ Pixel Noise ~ 3-5 e⁻ ENC
 - ✓ FPN ~ 5-17 e⁻ ENC
- Efficiency
 - ✓ ≥ 99.5 %
 - ✓ Time walk correction
- Cluster multiplicity
 - ✓ Typically in the 1-2 range
- Resolution as expected
- Fake rate probably very low
 - ✓ (< 10⁻⁶, tbc)



MIMOSIS = a milestone for Higgs factories (5 μm / ≤5 μs)

From TowerJazz 180 nm (ALPIDE^{@ITS2} & MIMOSIS) to TPSCo 65 nm (ITS3)

- 65 nm feature size technology
 - ✓ (ALPIDE & MIMOSIS fabricated in 180 nm)
 - ✓ Larger wafers (⇒ 30 cm)
 - ✓ More functionalities inside the pixel
 - ✓ Keeps pixel dimensions small ⇒ spatial res.
 - ✓ Potentially faster read-out
 - ✓ Lower Power consumption
- **TJ-65 nm available** (since June 2020)
 - ✓ Main driver: CERN EP R&D WP 1.2 & ALICE ITS-3 upgrades (involves other labs) ⇒ LS3 ~ 2024-26
 - ✓ Different requirements
 - EP: time resolution and radiation tol.
 - ALICE: granularity and material budget
 - Common R&D during the 1st years.



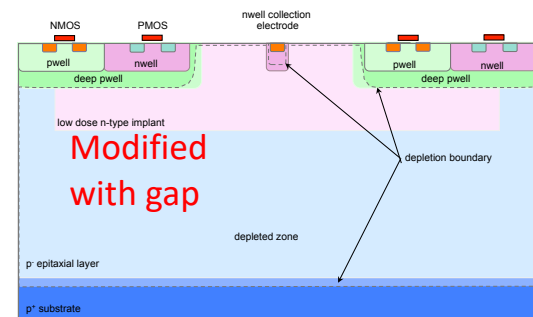
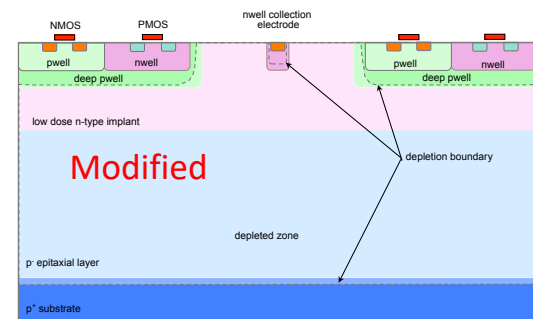
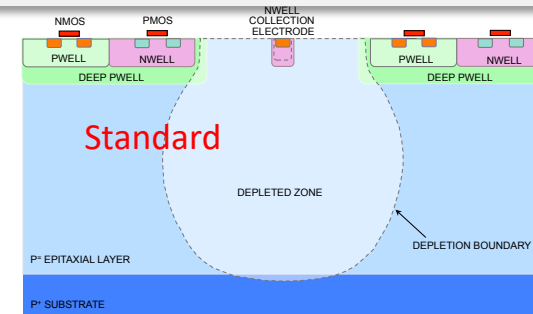
The search for the optimal variant : depletion and doping

- ✓ 3 process variations for depletion control:
 - Standard (no modifications)
 - Modified (low dose n-type implant)
 - Modified with gap (low dose n-type implant with gaps)
- ✓ 4 process splits:
 1. **Default**
 2. First intermediate optimization
 3. Second intermediate optimization
 4. **Fully optimized process**
- ✓ Lower power consumption
- ✓ Possibly better radiation hardness

⇒ First submission: MLR1 (Q4 2020)

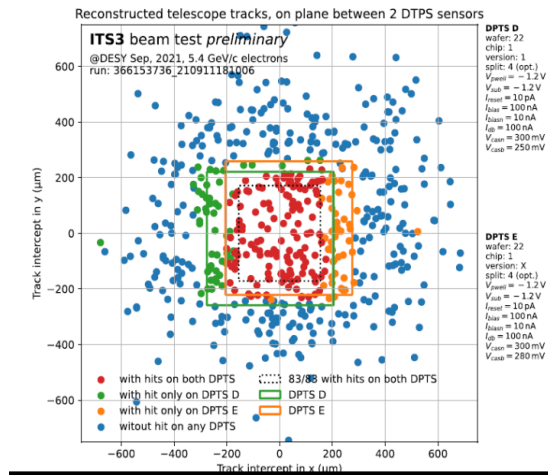
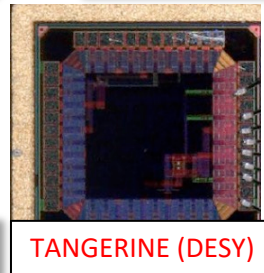
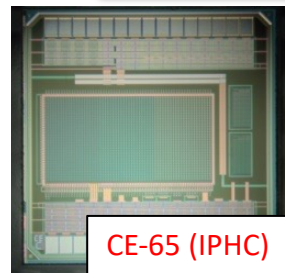
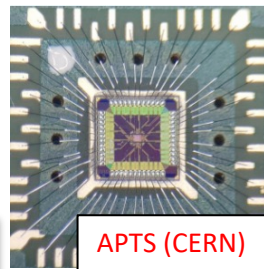
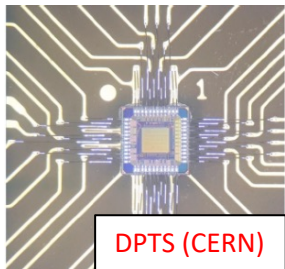
⇒ Synergy with Higgs factories requirements

⇒ Relation with foundries and access to options is a key factor

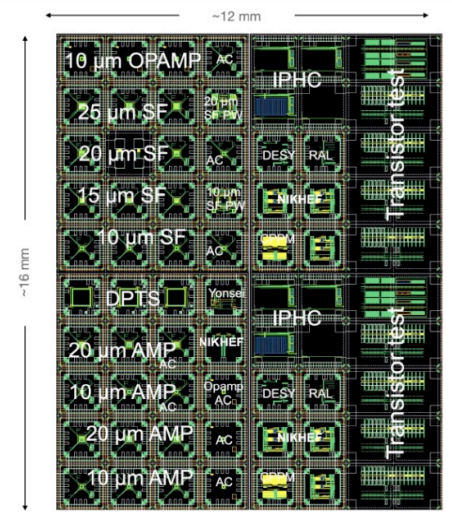


65nm MLR1

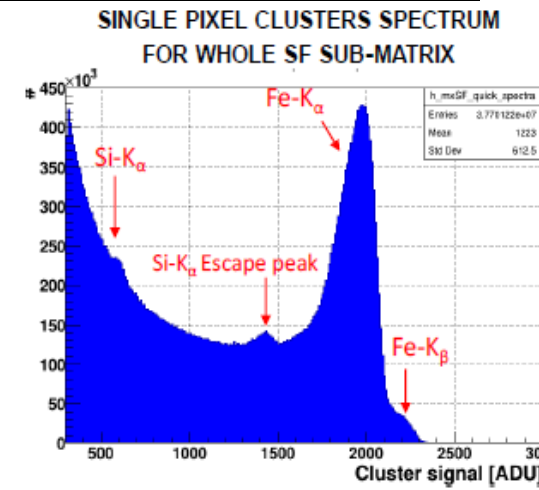
- Technology exploration
- Various pixel matrices and test structures
 - ✓ Radiation test structures
 - ✓ Amplification, DACs, LVDS, etc.
 - ✓ Pitch 15-25 μm
 - ✓ Epi variants



DPTS in test beam

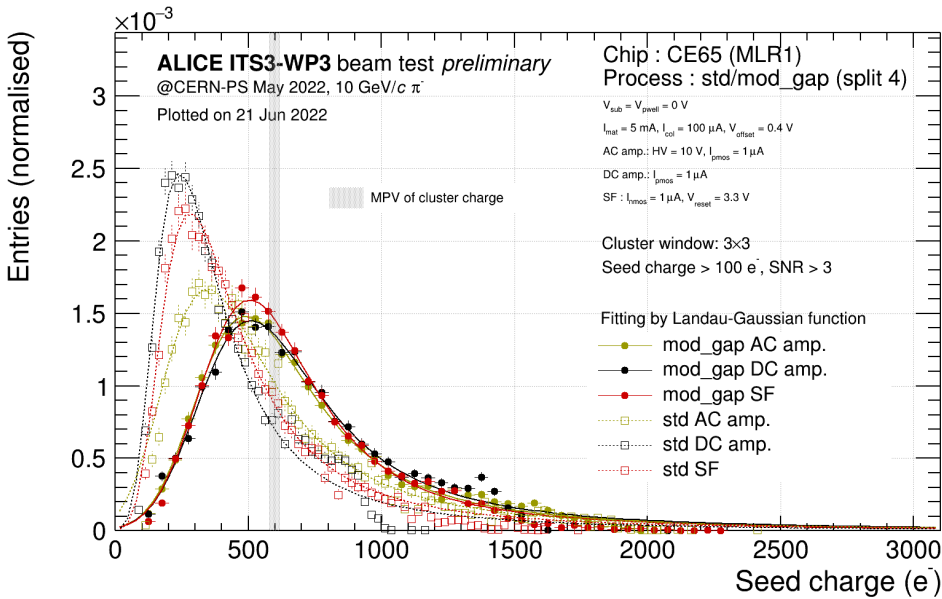
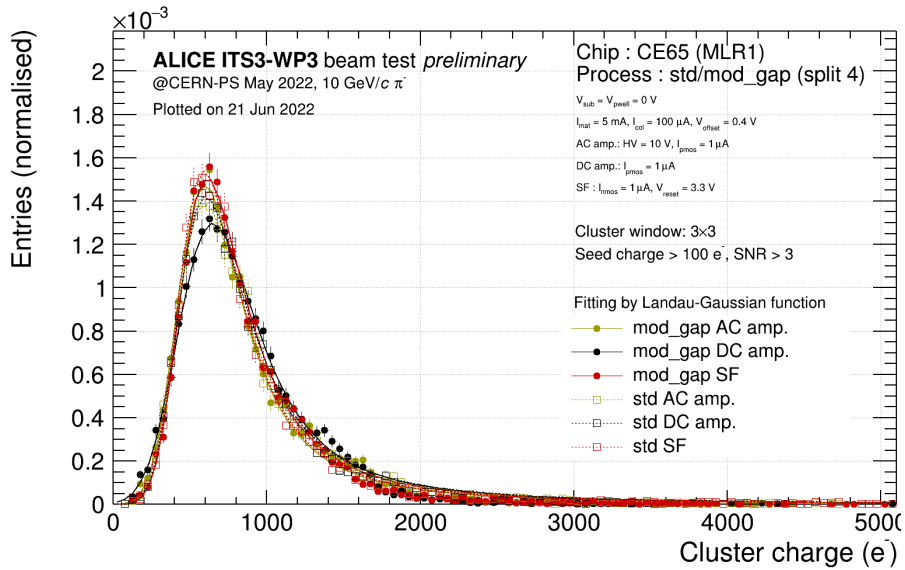


IPHC, CERN, DESY, NIKHEF, Ral, Yonsei



CE_65 with ⁵⁵Fe

CE65: Process modification reduces charge sharing



With modified process all the charge is mostly collected by a single pixel

- ✓ Excellent charge collection efficiency
- ✓ Epi variants induce different charge sharing profile -> Resol Optimisation
- ✓ Epitaxial layer thickness estimates match expectations

Sensors with timing precision $< 1 \mu\text{s}$

MIMOSIS-0fast prototype sensor

- Fabricated in mid-2022
- Derived from MIMOSIS architecture with faster front-end
- Explore timing in range 100-500 ns with power dissipation $\ll 100 \text{ mW/cm}^2$
- 32x504 pixels ($27 \times 30 \mu\text{m}^2$)

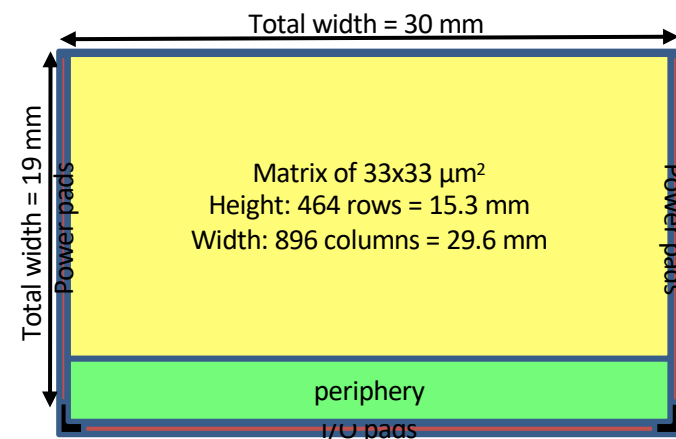


14.8 x 2.0 mm²

OBELIX sensor Belle II upgraded VXD

- First version submission end of 2022
- Large collab: Bonn, CPPM, HEPHY, INFN, IPHC, Valencia
- Extension of TJ-MONOPIX-2 issued from R&D for ATLAS-ITK

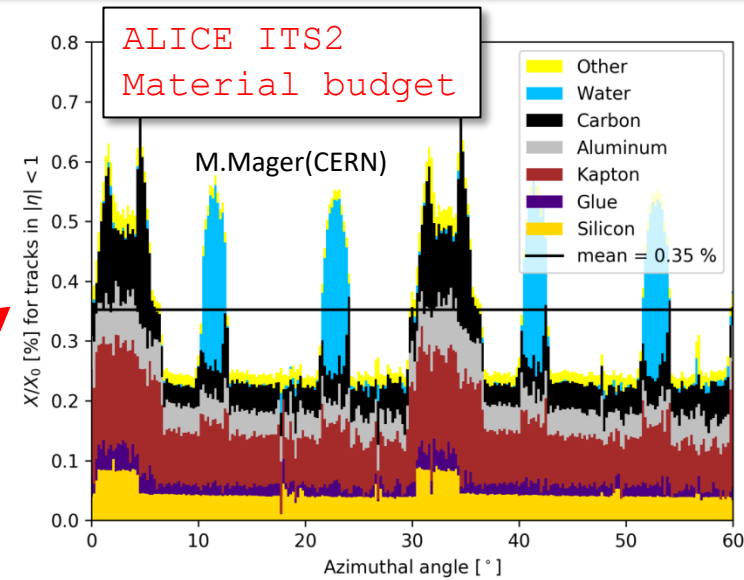
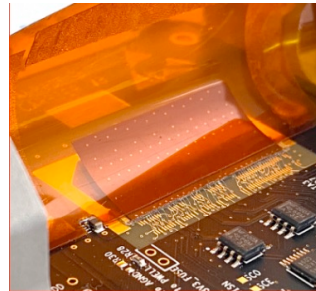
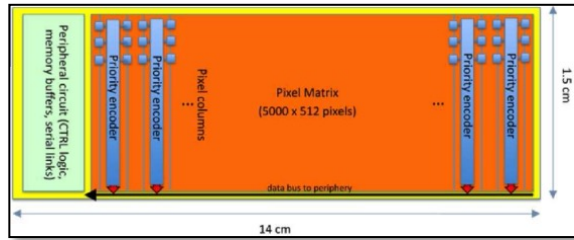
	OBELIX
Pitch	33 to 40 μm
Signal ToT	7 bits
Time stamp	7 bits
Integration time	25 To 100 ns
Bandwidth	$< 1 \text{ Gbps}$
Power	$< 200 \text{ mW/cm}^2$



Material budget: Bent sensors & stitching

Stitching:

- ✓ The way to go to minimize material budget



ALICE-ITS3/CERN drive the R&D

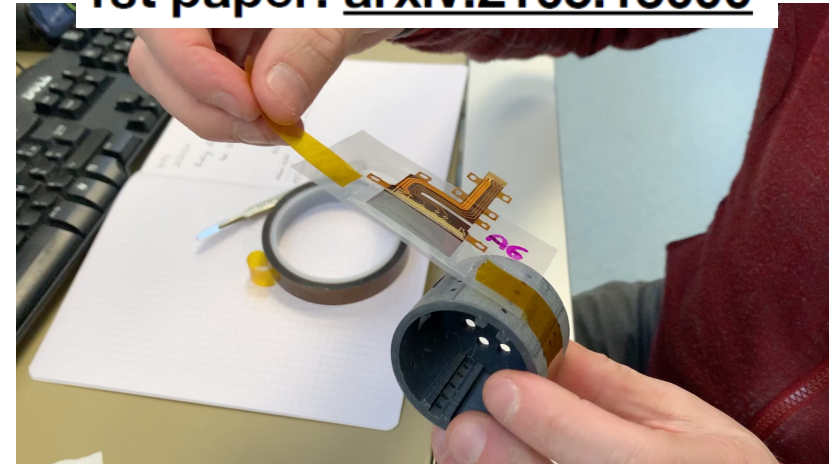
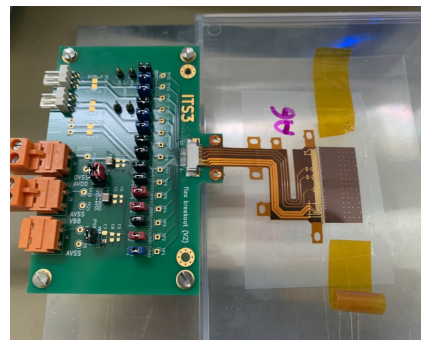
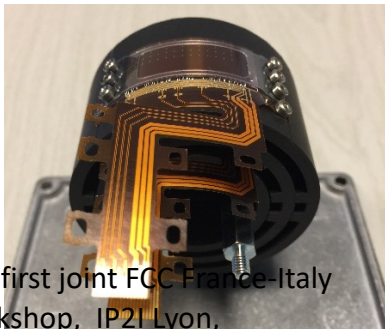
- ✓ Cf. M. Mager Seminar: *ALICE ITS3 - a next generation vertex detector based on bent, wafer-scale CMOS sensors*

▪ <https://indico.cern.ch/event/1071914/>

Micro-technics tests @IPHC

- ✓ collaboration with ALICE-ITS3
- ✓ Know-how acquired for bent bonding.

1st paper: [arxiv:2105.13000](https://arxiv.org/abs/2105.13000)



Bending / bonding
Or Bonding / bending
⇒ Functional tests

Conclusion & Synergies in CMOS R&D

- Integration \Rightarrow not discussed here!
- CMOS Pixel Sensors are the baseline for Higgs factories
 - ✓ Requirements are within reach
- Strong dynamic of CMOS pixel Sensors R&D:
 - ✓ **180 nm : MIMOSIS series**
 - (5 μ m spatial res./ \leq 5 μ s time res./ 60 μ m thickness / < 70 mW/cm²)
 - MIMOSIS-1 \Rightarrow full size prototype being tested
 - MIMOSIS-2 to be submitted (Q3 2022)
 - ✓ **65 nm technology exploration**
 - First submission dec.2020 (MLR1)
 - **First test beam on CE_65 chips @ CERN/DESY \rightarrow promising first results**
 - **2nd submission (ER1, Q1 2022): Stitching**
 - ✓ **Stitching** & large surfaces for very low mass detectors \Rightarrow Priority for Higgs factories in the future
 - Bent sensors test beam performed by ALICE
 - Material budget & Large pixelated surfaces
 - ✓ **Synergies** with
 - CERN R&D (ALICE ITS upgrades and EP R&D WP1.2)
 - R&D programs (e.g. AIDA-Innova, EURIZON, etc.)
 - Heavy ion experiments (e.g. ALICE beyond LS3/4 proposal, CBM, EIC)
 - Other experiments: Belle-II, etc.

Thanks for your attention